

- 🌀 L22: (3298) 7 near2 20
- 🌀 L23: (12) 21 and 22
- 🌀 L24: (34) "UNITED EPITAXY".as.
- 🌀 L25: (181448) sin silicon adj nitride
- 🌀 L26: (238057) amorphous
- 🌀 L27: (1187) 28 adj 25
- 🌀 L28: (0) 21 and 27
- 🌀 L29: (0) 27 with 9
- 🌀 L30: (18) 27 with 20
- 🌀 L31: (6827) lattice adj match\$4
- 🌀 L32: (0) 27 with 31
- 🌀 L33: (0) 27 same 31
- 🌀 L34: (0) 27 same 8
- 🌀 L35: (4158134) el aluminum
- 🌀 L36: (4572722) al aluminum
- 🌀 L37: (264544) nitride
- 🌀 L38: (39832) 38 adj 37 aln
- 🌀 L40: (5) 16 and 39
- 🌀 L39: (32) 38 same 27
- 🌀 L41: (124240) silicon adj substrate
- 🌀 L42: (4) 14 same 41
- 🌀 L43: (445) 41 same 16
- 🌀 L44: (34559) sapphire
- 🌀 L45: (523) 41 near9 44
- 🌀 L46: (34) 43 and 45
- 🌀 L47: (38) 40 48

US:PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

Default operator:

☐ Plurals

☐ Highlight all hit terms initially

40 48

Dec-2004

U	I	Inventor	Document#	Issue	P	Title	Current	CurrentXR	Retrieval	S	C	P	U	I	Image Doc.	P	
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Iskida, Masah	US 9420197	20020	2	Semiconductor device and method of fabrica	438/22	257/10		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 9420197	<input checked="" type="checkbox"/>
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Temkin, Henri	US 6391749	20020	1	Method of epitaxial growth of high quality ni	438/478	257/E21.12		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6391749	<input checked="" type="checkbox"/>
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Letierre, Fab	US 2004024	20041	9	Substrate for stressed systems and method o	438/108			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2004024	<input checked="" type="checkbox"/>
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Nishikawa, T	US 2004022	20041	2	Layered structure, method for manufacturing	438/202			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2004022	<input checked="" type="checkbox"/>
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Weeks, T. W	US 2004013	20040	4	Gallium nitride material devices and methods	257/622	257/E29.31		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2004013	<input checked="" type="checkbox"/>
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Kong, Hua-Sh	US 2004008	20040	2	Single step pendeo-and lateral epitaxial over	438/491	257/E21.11		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2004008	<input checked="" type="checkbox"/>
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Sawaki, Nob	US 2004006	20040	9	Semiconductor element structure, electron e	257/103			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2004006	<input checked="" type="checkbox"/>
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Kong, Hua-Sh	US 2003020	20031	2	Single step pendeo- and lateral epitaxial over	438/200	257/E21.11		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2003020	<input checked="" type="checkbox"/>
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Iskida, Masah	US 2003018	20031	4	Semiconductor substrate, method of manufa	257/94	438/22		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2003018	<input checked="" type="checkbox"/>
10	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Saxler, Adam	US 2003010	20030	1	Strain balanced nitride heterojunction transi	257/85	257/E29.24		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 2003010	<input checked="" type="checkbox"/>